

EAST - (10790760 yttrium doped BST hi dielectric film for capacitor.wsp.1)

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8 near 4 58

May 2005

U	Inventor	Document	Issued	Title	Current	Current	Retrieval	S	C	P	Image	Doc
1	Devoe, Daniel	US 200301	2003	2	Ceramic chip capacitor of conventional	361/32						US 200301
2	Devoe, Daniel	US 200301	2003	2	Ceramic chip capacitor of conventional	361/32						US 200301
3	Amatsuchi, US	200200	2002	15	Plasma display panel	313/58						US 200200
4	Harui, Seiji	US 200100	2001	71	Dynamic random access memory (DRAM)	365/14	257/E27.0					US 200100
5	Kar-Roy, Arj	US 677777	2004	10	High density composite MIM capacitor	257/53	257/310:					US 677777
6	Devoe, Daniel	US 675321	2004	27	CERAMIC CHIP CAPACITOR OF CONVENTIO	438/24	361/23:					US 675321
7	Devoe, Daniel	US 675108	2004	2	CERAMIC CHIP CAPACITOR OF CONVENTIO	361/32	361/306.1:					US 675108
8	Amatsuchi, US	683836	2003	14	Plasma display panel	313/58						US 683836
9	Ng, Chit Hw	US 662404	2003	12	Self-Integrated vertical MIM capacitor	438/42	257/E21.01					US 662404
10	Devoe, Daniel	US 654235	2003	27	CERAMIC CHIP CAPACITOR OF CONVENTIO	361/32	361/306.1:					US 654235

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